



# BONDABILITY RELATED TO PROBING

« WHEN PROBING AND BONDING ARE NOT GOOD FRIENDS ! »

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and Dominique LANGLOIS  
with Patrick BUFFEL



## AGENDA

### Part 1/4 Impact of probing on wire bonding

- Introduction of Infineon plants
- Ball bonding sequence and failure mode
- Data collection and analysis

### Part 3/4 Probe-card improvements

- How to improve Cantilever (APS/MJC)
- Low pitch micro-spring PC for tomorrow (FFI)

### Part 2/4 Probing process

- Altis Semiconductor presentation
- Final sort process flow
- Why several touch downs...
- Probe marks size, build-up height, exposed-oxide mechanisms

### Part 4/4 Conclusion

- Bonding concerns
- What could be the solutions...

# Infineon (Corporate Back End - CBE)

## Overview

**Assembly & Test:** Logic & Power Ics / Discretes / Optocoupler / High frequency Components & Sensors  
**Employees:** 7510  
**Area:** 111 400 m<sup>2</sup>

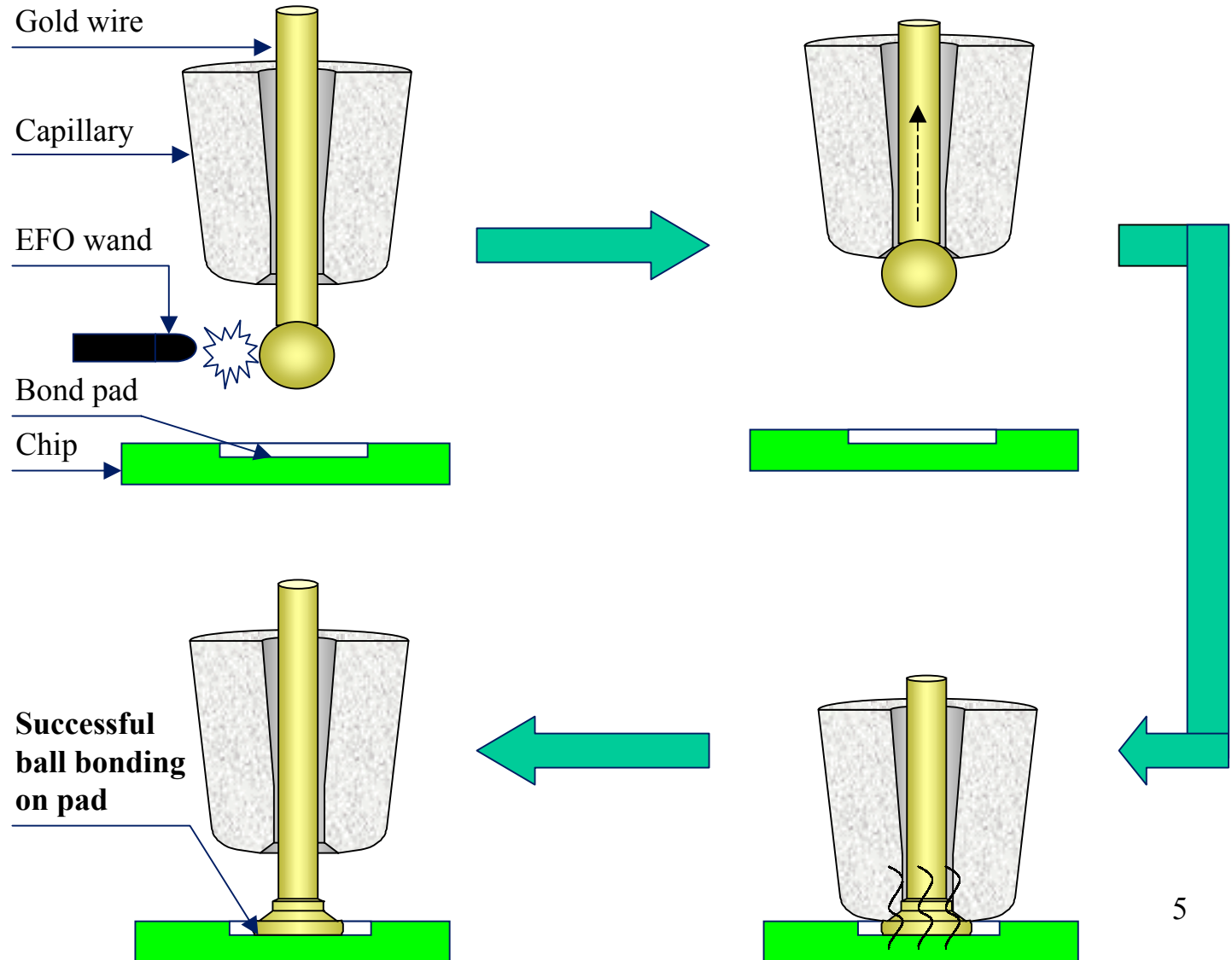


# Singapore - Assembly & Final Test of Logic ICs

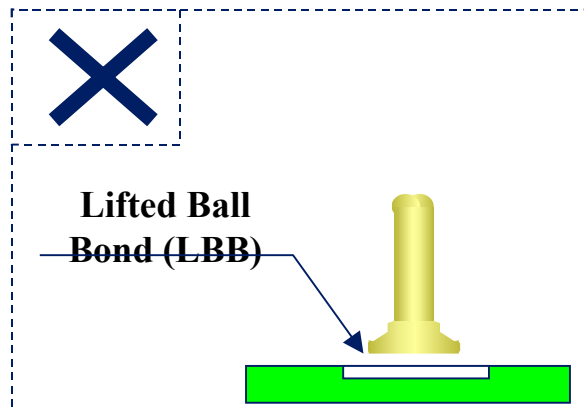
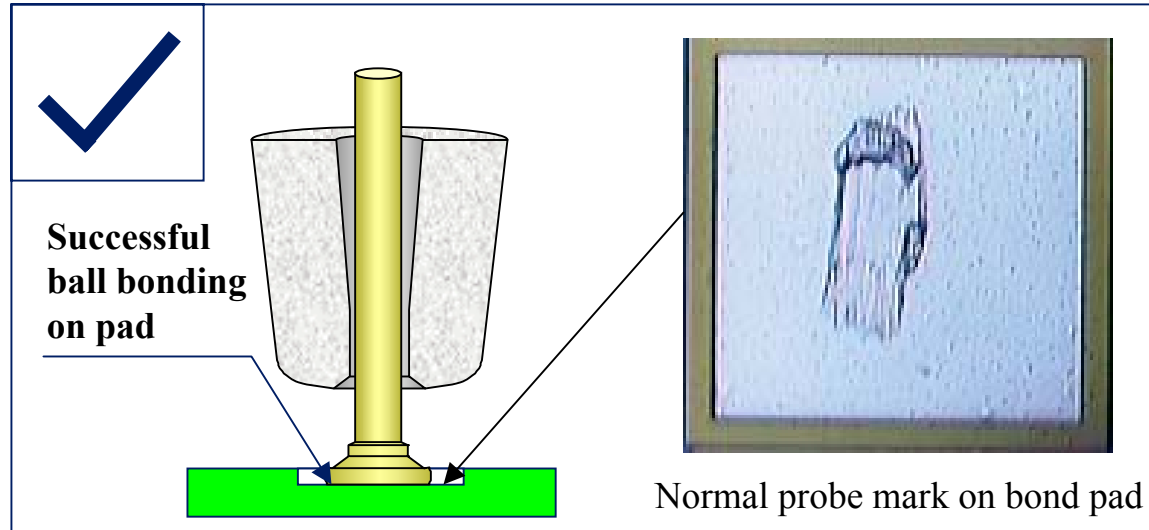


<b>Country:</b>	Singapore
<b>Products:</b>	Applications Specific ICs Microcontrollers Power ICs High Frequency ICs
<b>Packages:</b>	P - TSSOP P - MQFP P - TQFP P - LFBGA P - VQFN
<b>Testers:</b>	Logic, Analog & Mixed Signal
<b>Production* :</b>	583' (pieces 00/01)
<b>Employees:</b>	2000 (without Sales,DC,EZM & AIT)
<b>Floor space:</b>	31410 m <sup>2</sup>
<b>Established:</b>	1993 (Founded 1970)

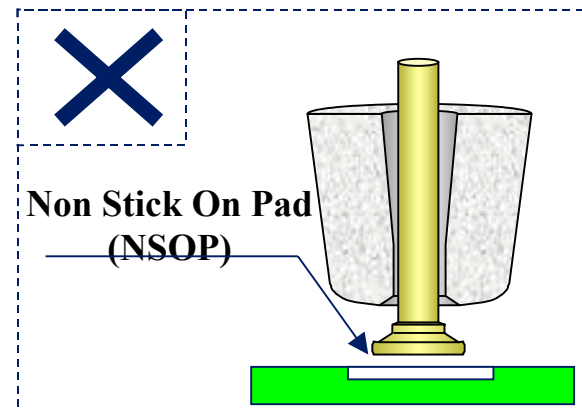
# Wire bonding (thermosonic) on the bond pad - Ball bonding sequence



# What is Lifted Ball Bond (LBB) & Non Stick On Pad (NSOP)?

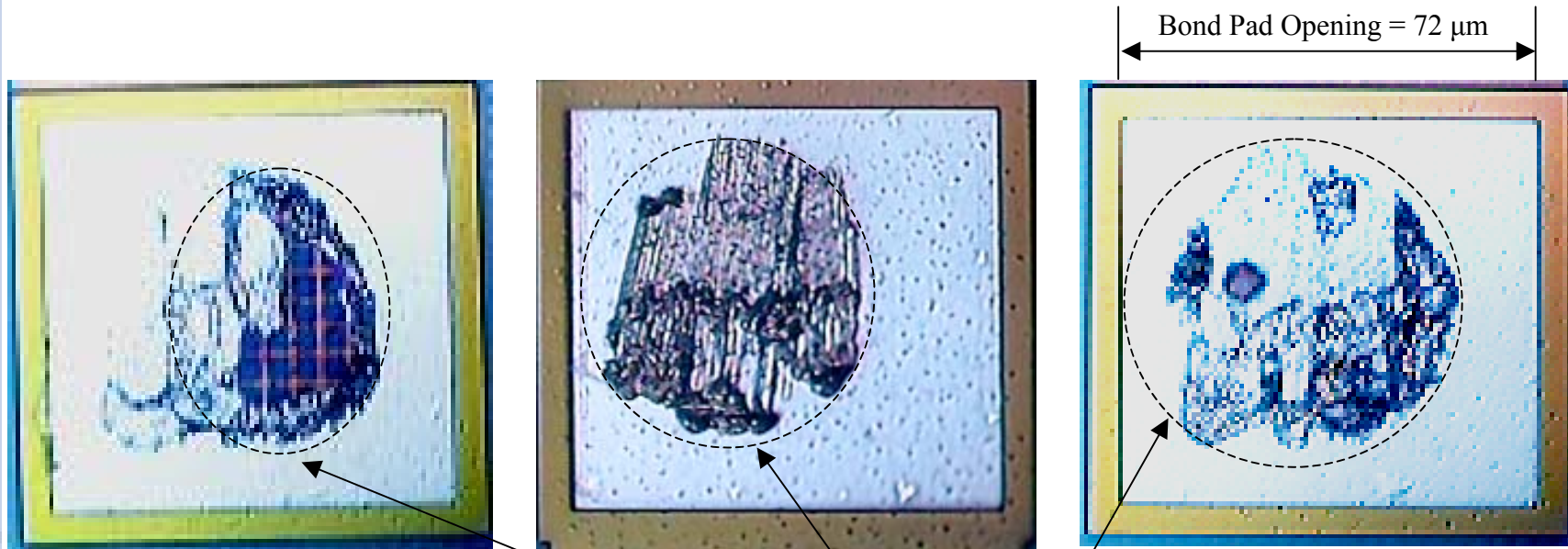


Ball bond is lifted after wire bonding

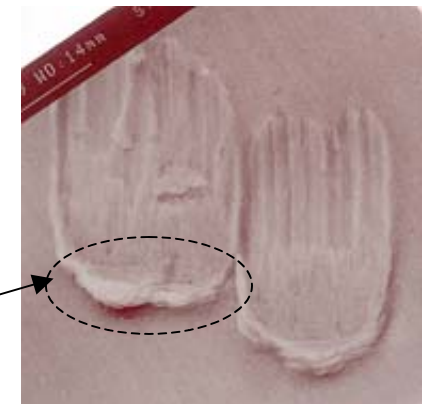


Ball bond is lifted during wire bonding

# What can cause Lifted Ball Bond (LBB) & Non Stick On Pad (NSOP)?

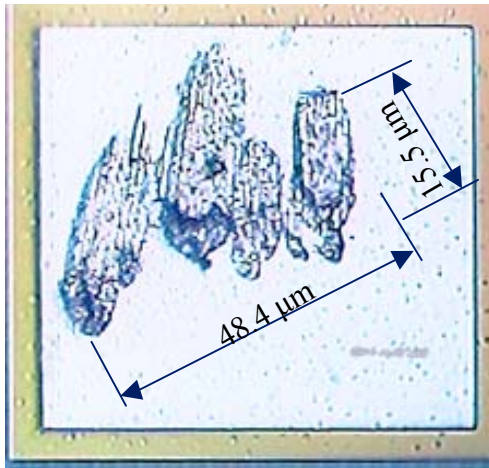


- 1. Exposed Oxide**
- 2. Big/Multiple probe marks**
- 3. Aluminum build-up**



# Classification of exposed oxide, big probe marks, and Aluminum build-up

## Probe Mark measurement



Probe mark area  
 $= 48.4 \times 15.5$   
 $= 750.2 \mu\text{m}^2$

% of probe area vs bond pad opening  
 $= 750.2 / (72 \times 72)$   
 $= 750.2 / 5184$   
 $= 14.5\%$

## Exposed Oxide measurement

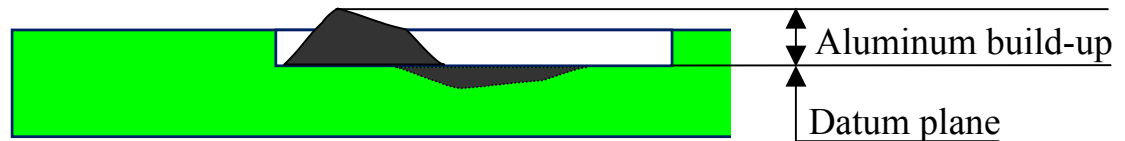


Exposed oxide area  
 $= (3.14 \times 6.68 \times 6.68) / 4$   
 $= 35.03 \mu\text{m}^2$

% of exposed oxide area vs bond pad opening  
 $= 35.03 / (72 \times 72)$   
 $= 35.03 / 5184$   
 $= 0.68\%$

Diameter = 6.68μm

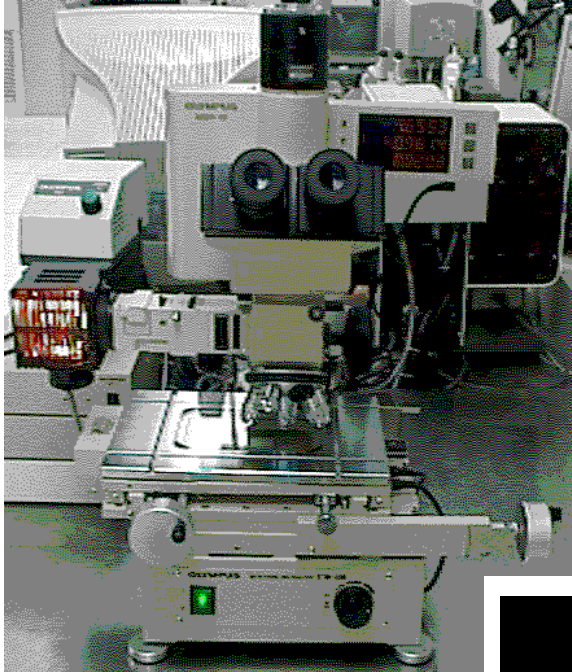
## Aluminum Build-Up measurement



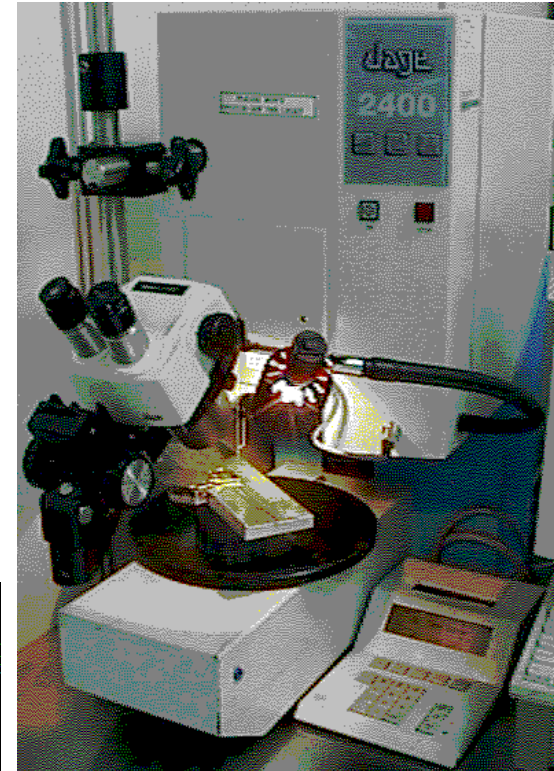
1. Focus is done on the selected bond pad, making it the datum plane.
2. Move the scope vertically in the z-axis to focus on the tip of the build-up.
3. This vertical displacement is the height of the Aluminum build-up.



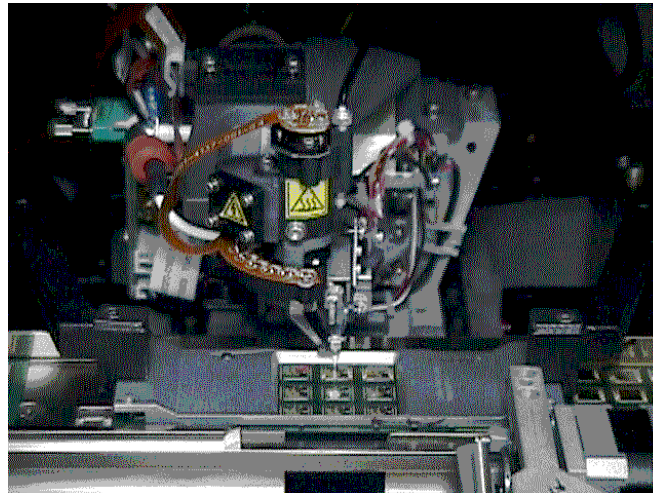
# Instruments used for non-destructive (dimensioning) and destructive tests (ball shear)



Microscope

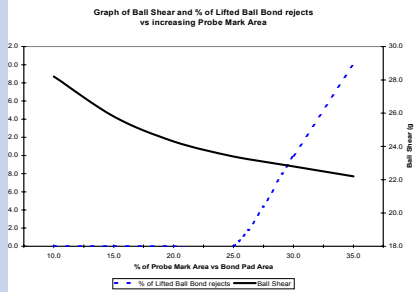


Ball shearing machine

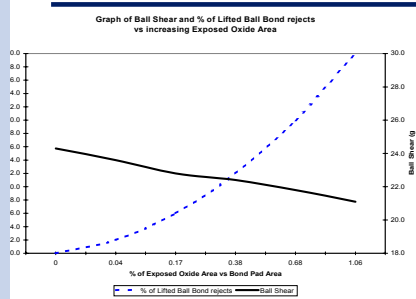


Wire bonding machine

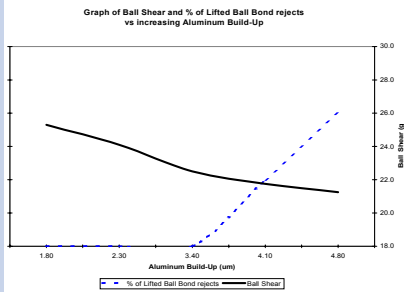
# What is the impact of Ball Shear and % of Lifted Ball Bond on bond pads with big/multiple probe marks?



# What is the impact of Ball Shear and % of Lifted Ball Bond on bond pads with exposed oxide?



# What is the impact of Ball Shear and % of Lifted Ball Bond on bond pads with Aluminum build-up?



- **A Company built from the IBM Microelectronics Corbeil-Essonnes site**
- **50 / 50 IBM / Infineon Joint Venture ( 07 / 99 )**
- **A conversion from DRAM centric focused product mix to Logic centrix focused mix**
  - ✓ LOGIC : 0.35 $\mu$  / 0.25 $\mu$  Aluminium / 0.18 $\mu$  Copper / 0.13 $\mu$  Copper Low K
  - ✓ Embedded MEMORY: DRAM 0.35 $\mu$  / 0.20 $\mu$  / 0.17  $\mu$
- **World class customers leaders in Telecoms and Computer peripherals**
- **Shared management IBM / Infineon**
- **Capacity sharing 50 / 50 based on normalized capacity**
- **Investment plan : about 1 Billion Euro in the years 2000/2001**

## WHEN PROBING AND BONDING ARE NOT GOOD FRIENDS !



**NEGATIVE FOR  
BONDING**

Decrease Bonding  
Performance



JUNE 6, 2001  
San Diego SWTW

**SCRUB MARK EFFECTS**

- Remove alu oxide
- Decrease CRs
- Improve Yield
  
- Allow Prober to  
operate needle to pad  
alignment

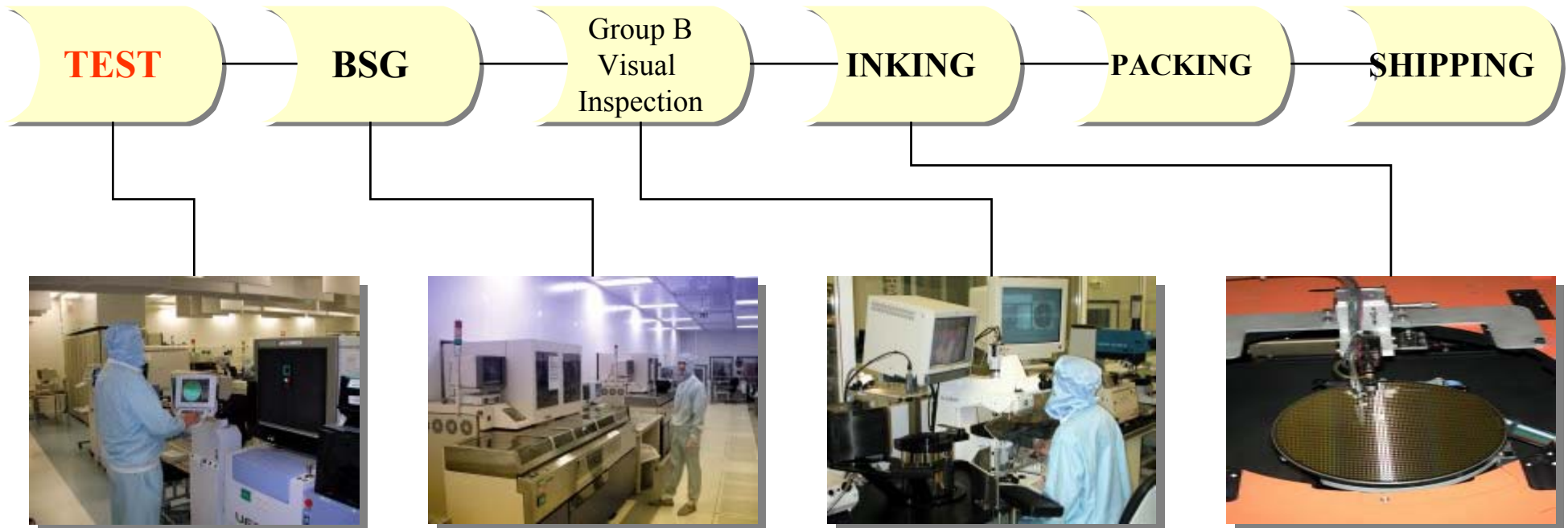


**POSITIVE FOR  
TESTING**



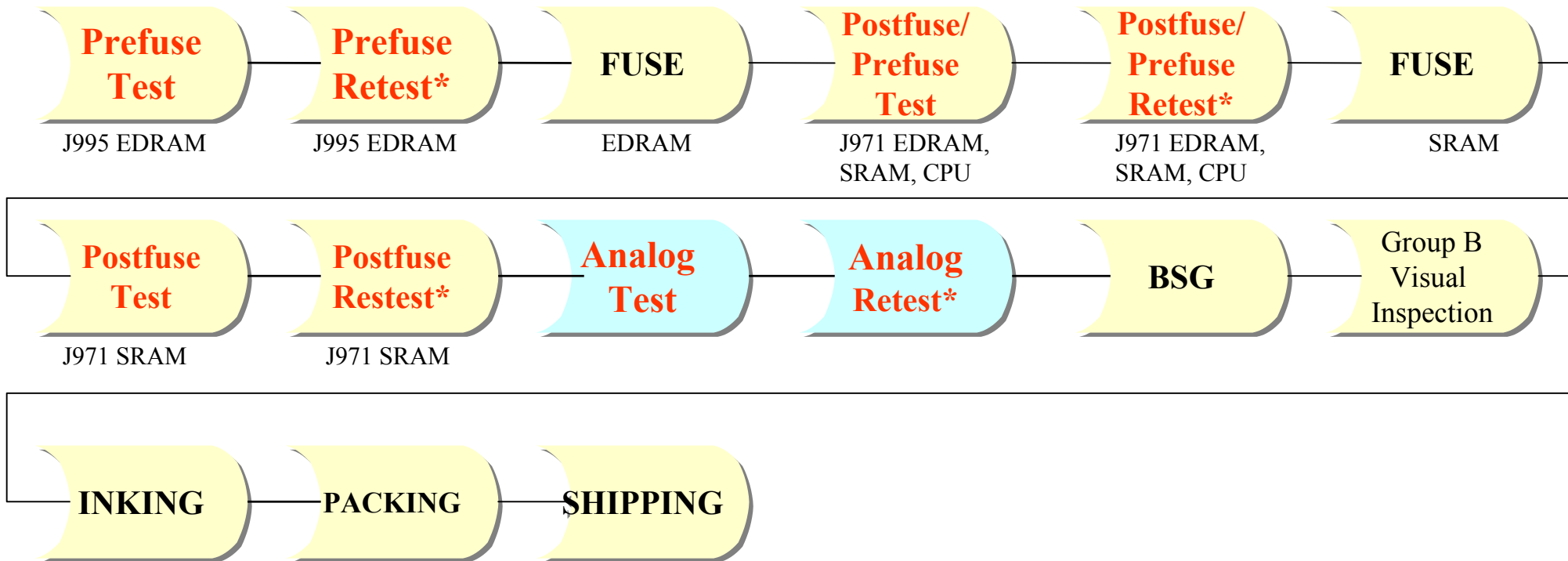
## FINAL SORT : FROM SHORT TO LONG PATH...

Exemple 1 : The short way...



## WAFER SORT : FROM SHORT TO LONG PATH...

Exemple 2 : A long way to go...(logic product with EDRAM, SRAM, CPU)



\* If more than 5 % retest gain



## WHY SEVERAL PROBE MARKS...

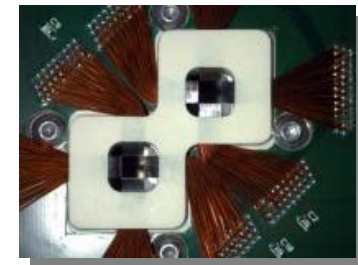
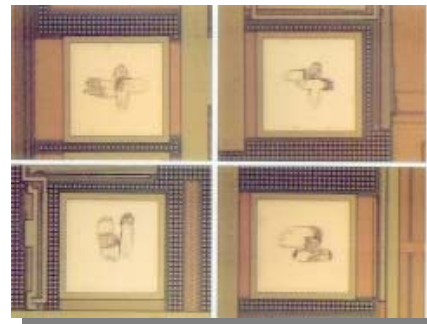
⇒ PROCESS REASONS :

- Different tests (Prefuse, Postfuse, Analog)
- Restest (contact problems, yield issues)...



⇒ PROBE-CARD REASONS :

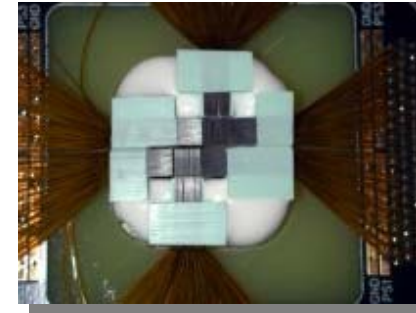
- Over probing due to probe-card (Dut layout)



## WHAT MAKES THE SIZE OF A PROBE-MARK...

### ⇒ PROBE-CARD REASONS :

- Tip size, tip shape
- Needles planarity, PC warping (temperature)
- Needle gram force



### ⇒ PROBER REASONS :

- Z height detection, profiler precision
- Chuck, prober table planarity
- Test head docking influence



### ⇒ PRODUCT REASONS :

- Pad material hardness

### ⇒ HUMAN REASONS :

- Overtravel set by operator



## HOW CAN EXPOSED OXIDE HAPPENED ?

### ⇒ PROBE-CARD REASONS :

- Tip size, tip shape
- Needles planarity, PC warping (temperature)
- Needle gram force
- Scrub length (beam angle, needle layer related)

### ⇒ PRODUCT REASONS :

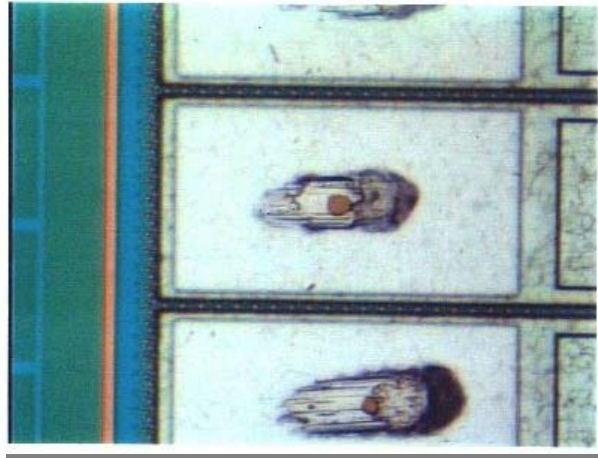
- Pad thickness (technology dependant)
- Pad material hardness
- Pad structure

### ⇒ PROBER REASONS :

- (same as page 18)
- Double Zup
- Z chuck speed

### ⇒ HUMAN REASONS :

- Excessive overtravel set by operator



## **AND WHAT ABOUT THE SCRUB MARK BUILD-UP HEIGHT !**

**A VERY DIFFICULT AND NEW PARAMETER TO CONTROL AND UNDERSTAND  
(SO FAR NO PROBE-CARD SPECIFICATIONS LINK TO THIS PARAMETER..)**

⇒ **PROBE-CARD REASONS :**

- Needle shape (flat, radius, semi-radius, beam angle)
- Needles planarity, PC warping (temperature)
- Needle gram force
- Beam, knee, taper angle

⇒ **PRODUCT REASONS :**

- Pad material hardness

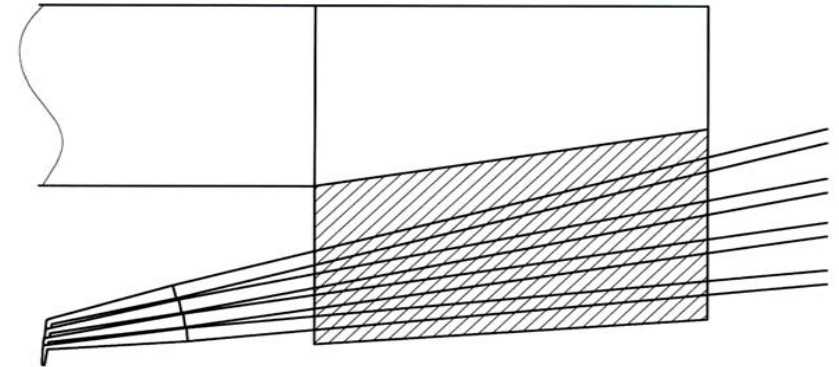
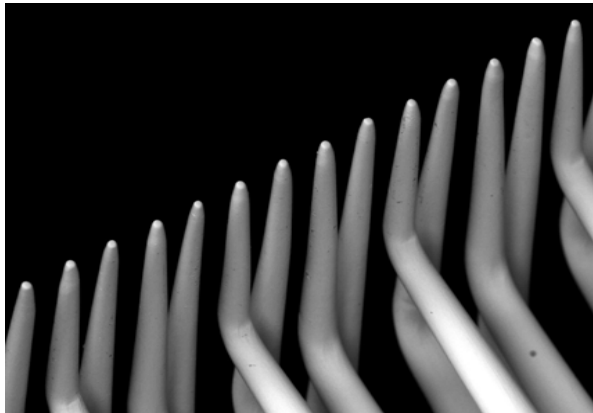
⇒ **PROBER REASONS :**

- (same as on previous pages)

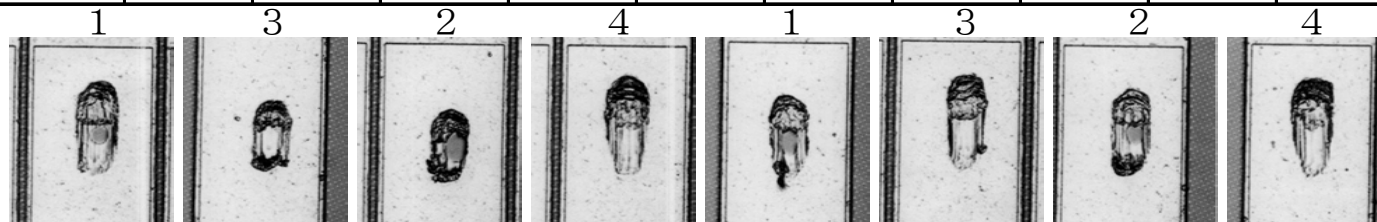
⇒ **HUMAN REASONS :**

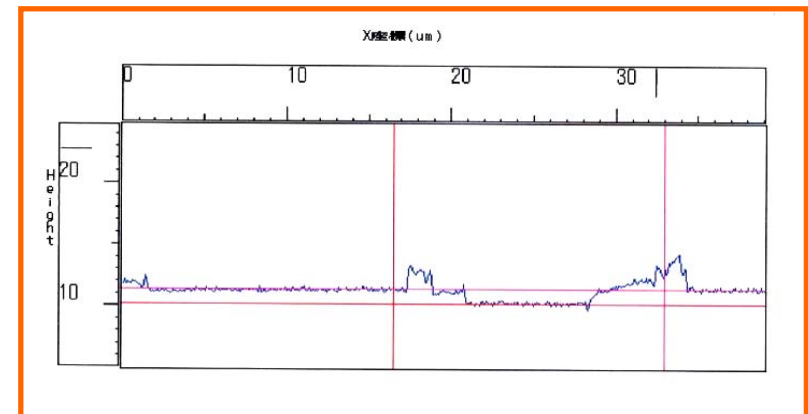
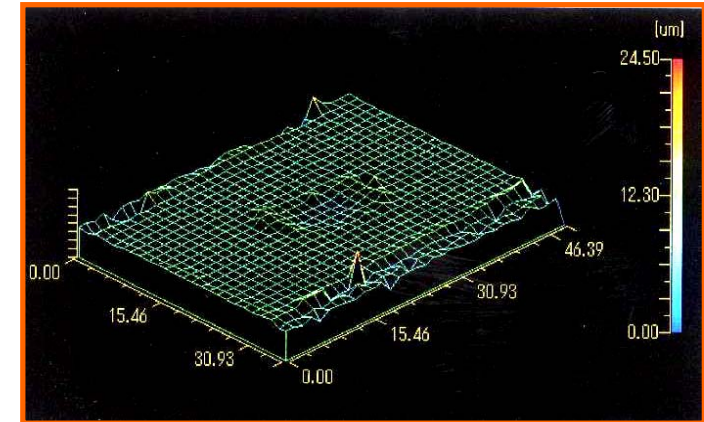
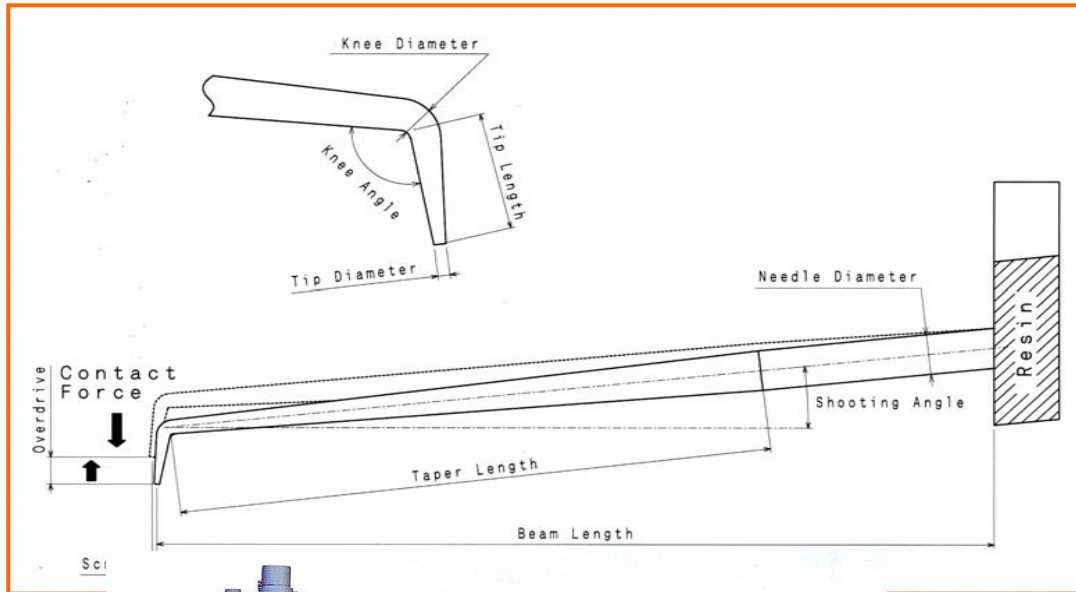
- Overtravel set by operator

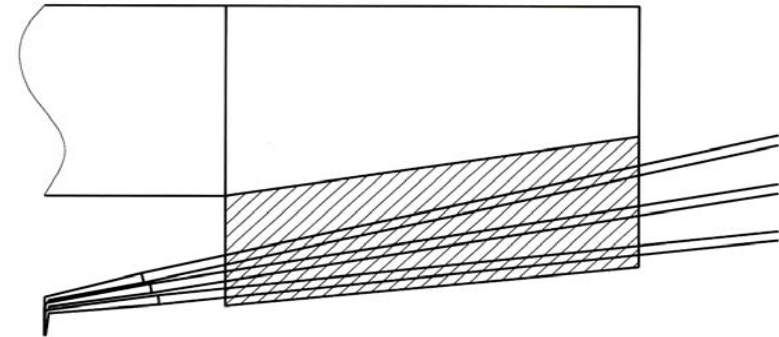
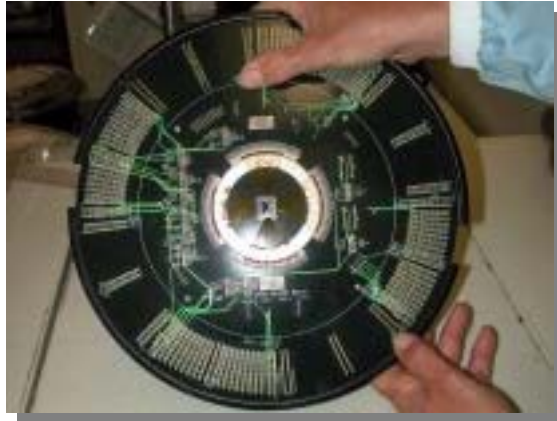
PAD PITCH 60um PAD SIZE 52x95um



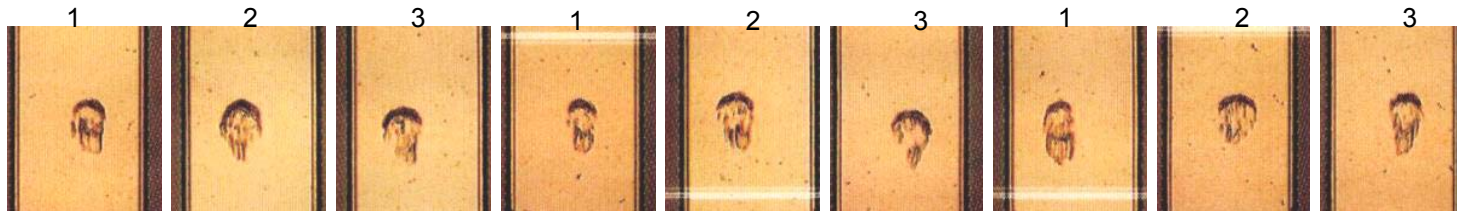
Layer	Needle Diameter ( $\varphi$ )	Angle	O/D ( $\mu\text{m}$ )	Tip Length ( $\mu\text{m}$ )	Beam	Knee	Taper	Contact Force (g)	Scrub amount ( $\mu\text{m}$ )	Remark
1	0.15	5	100	170	2763	0.050	1.5	9.37	13.96	28.96
2	0.15	7	100	250	2763	0.050	1.5	9.37	20.35	35.35
3	0.15	9	100	350	2763	0.055	1.5	9.69	27.55	42.55
4	0.15	11	100	450	2763	0.060	1.5	9.98	34.78	49.78



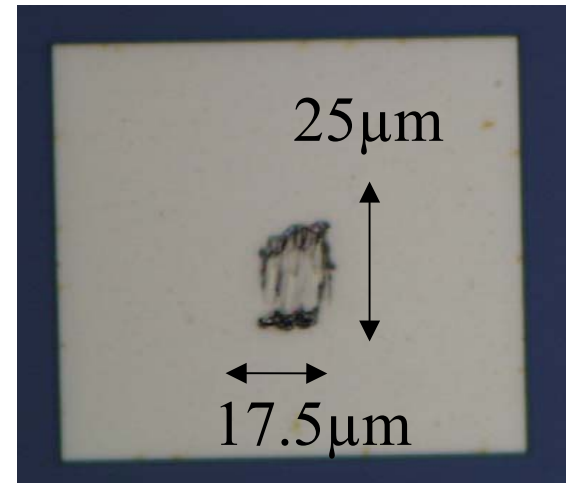
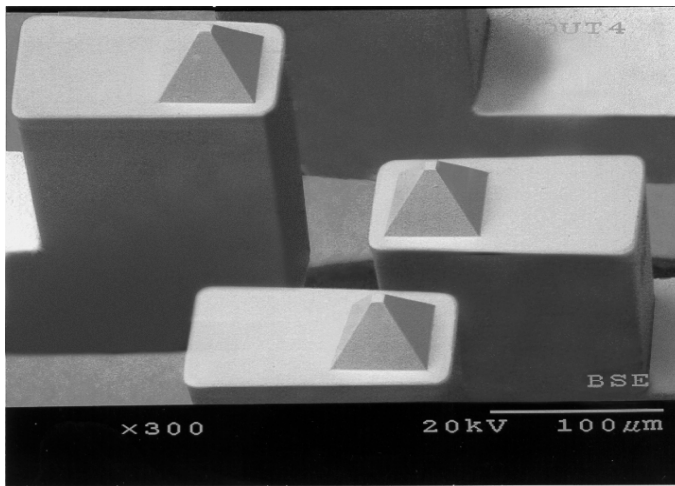




Layer	Needle Diameter ( $\varphi$ )	Angle	O/D ( $\mu\text{m}$ )	Tip Length ( $\mu\text{m}$ )	Beam	Knee	Taper	Contact Force (g)	Scrub amount ( $\mu\text{m}$ )	Remark
1	0.1	6	70	230	1749	0.044	1.134	5.01	13.57	28.57
2	0.1	8	70	290	1749	0.048	1.088	5.35	18.79	33.79
3	0.1	10	70	350	1749	0.051	1.042	5.6	21.91	36.91



# Fine Pitch Probing Critical Factor Probe Tip Size



100 μm  
pad

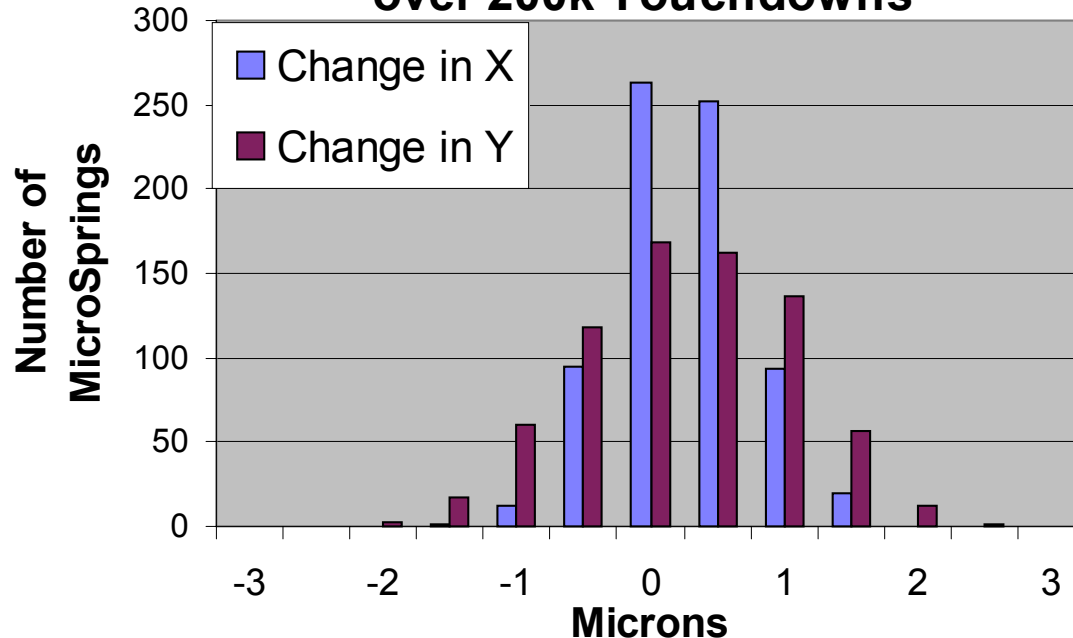
80 μm  
OT

- Controlling the probe tip size is critical for maintaining scrub mark size
- Fine pitch/Small pad probing may require  $< 10\mu\text{m}$  probe tips



# Fine Pitch Probing Critical Factor Alignment Repeatability

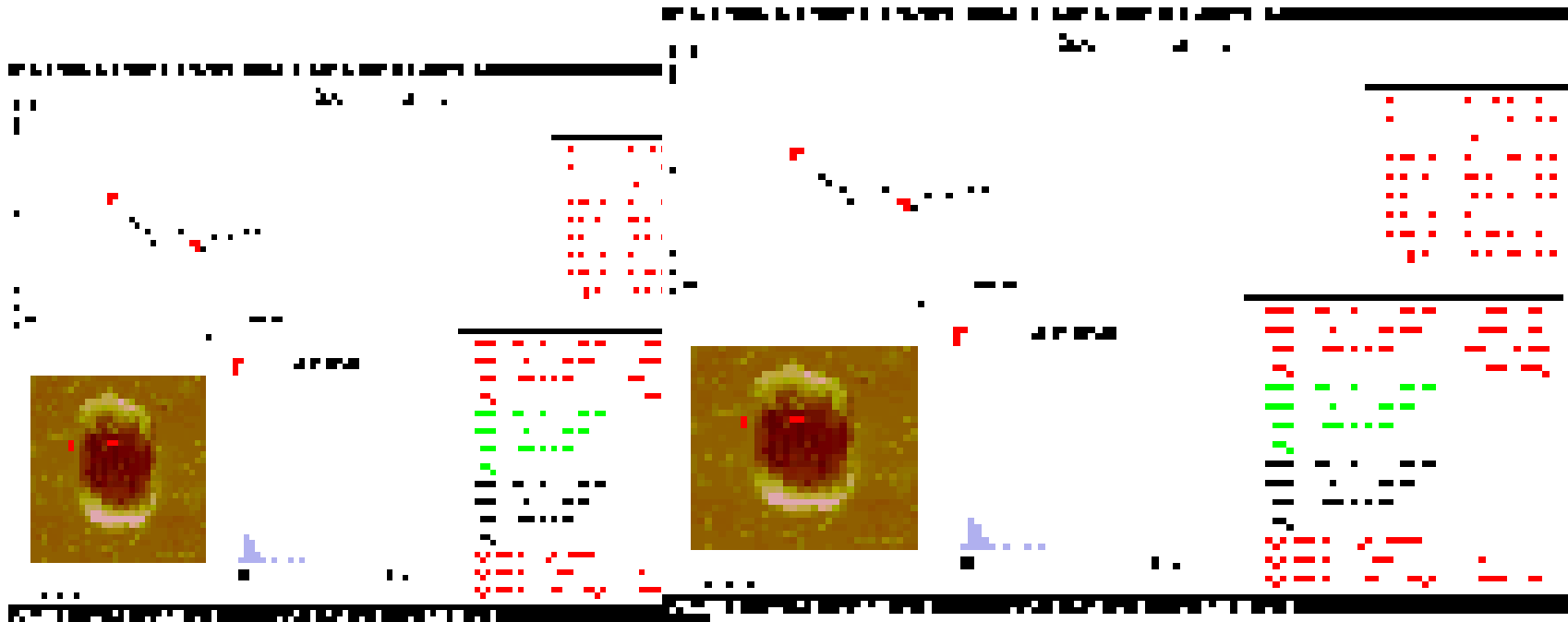
**Change in MicroSpring Alignment  
over 200k Touchdowns**



- Alignment variation leads to:
  - Passivation damage
  - Increased Maintenance
  - Yield loss
- Hitting the center of the pad is more critical for tighter pad pitch and smaller pads
- Alignment repeatability = **PRODUCTIVITY**

- 641 MicroSprings measured on API PRVX2  
 - Touchdowns performed at 75µm overtravel

# Fine Pitch Probing Critical Factor Pad Damage



- Scrub Depth – 500nm @ 40 $\mu$ m overtravel
- 10-15 $\mu$ m probe tip with 1.5gm/mil probe force

## CONCLUSION PART 1

1. The presence of big/multiple probe marks, exposed oxide & Aluminum build-up will cause:
    - 1.1 Ball shear readings to decrease.
    - 1.2 % of lifted ball bond rejects to increase.
  2. Probe mark area > 25% will increase lifted ball bond rejects.
  3. The presence of exposed oxide is already a reject, and it will exhibit lifted ball bond rejects.
  4. Aluminum build-up > 3.40um will increase lifted ball bond rejects.
- \* The simulation of probe mark defect modelling in this area will help to represent a more universal impact of wire bondability due to probing (the 3 elements covered).

**SHORT TERM SOLUTIONS**

- OPTIMIZE WAFER MAP INDEX (TO AVOID OVER PROBING)
- REDUCE PROBE-CARD SPECIFICATIONS
- PROBER IMPROVEMENTS :
  - IMPROVE PRECISION (calibration, preventive maintenance)
  - USE ALL POSSIBLE OPTIONS (soak time, double profiler, etc...)
  - REDUCE OVERTRAVEL LIMIT
- USE A PROBER / TESTER INTERACTIVE LOOP CONTACT
- USE WAFERWORX (API) TO OPTIMIZE PC SETUP
- CHARACTERIZE PROBING WITH WAFERS IN REAL PRODUCTION CONDITION



**LONG TERM SOLUTIONS**

- HAVING UNIVERSAL TESTERS (memory, analog and logic test)
- USE VERTICAL PROBING (to avoid scrubbing)
- FUSE DURING TEST (electrical fuse)
- WAFER SORT AFTER BONDING (exemple : WOW from FFI)
- PACKAGE TEST ONLY (using electrical fuse if needed)
- DEDICATED PAD FOR BONDING...
- ETC...

## ACKNOWLEDGEMENTS

### THANKS TO ALL PEOPLE INVOLVED IN THIS PRESENTATION

- Patrick BUFFEL (Altis Semiconductor)
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- Bob MARTIN (FORM FACTOR)

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